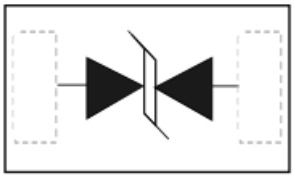
Description

The PESDR0521P1 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR0521P1 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±22kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR0521P1 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.



Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±25kV
    - Contact discharge: ±22kV
  - IEC61000-4-5 (Lightning) 4A (8/20μs)
- RoHS Compliant

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

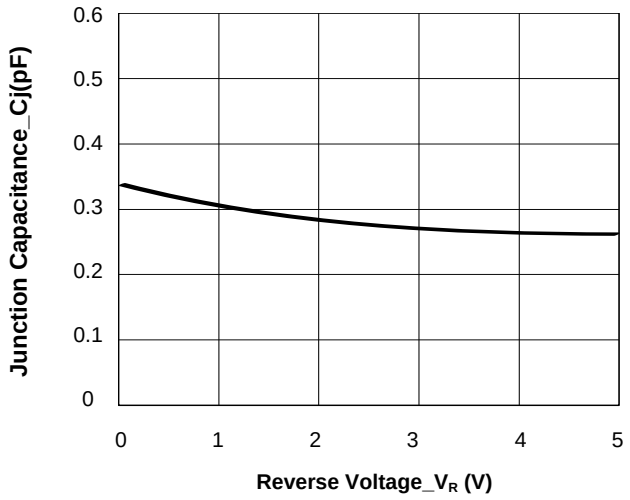
Absolute Maximum Ratings (T_A=25° C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P_{PK}	100	W
Peak Pulse Current (8/20μs)	I_{PP}	4	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±22	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

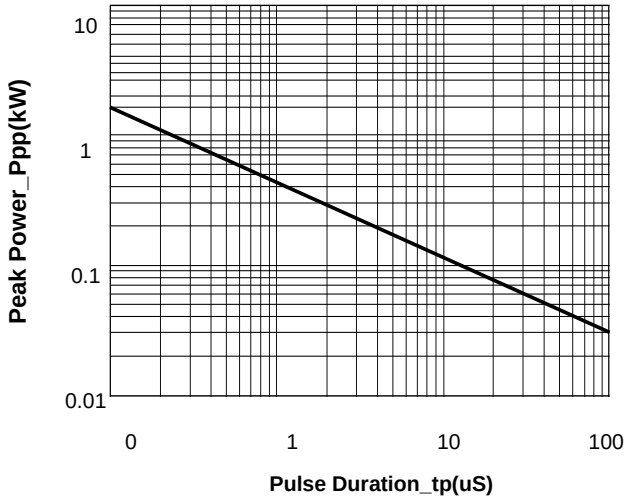
Electrical Characteristics (T_A=25° C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6.5		9.5	V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 5V
Clamping Voltage	V_C			12	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			25	V	I_{PP} = 4A (8 x 20μs pulse)
Junction Capacitance	C_J		0.3	0.5	pF	V_R = 0V, f = 1MHz

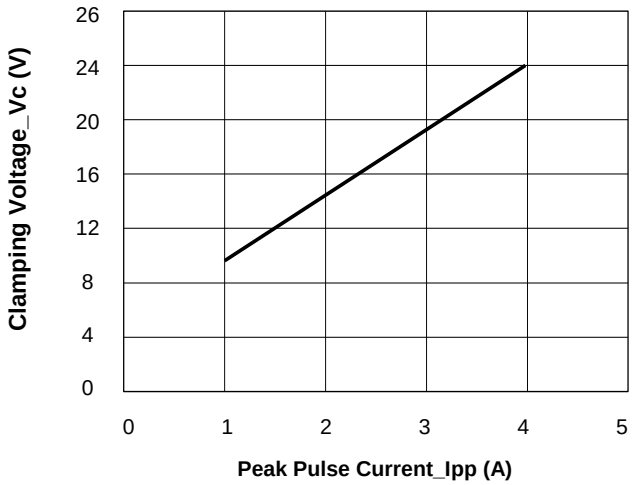
Typical Performance Characteristics (T_A=25° C unless otherwise Specified)



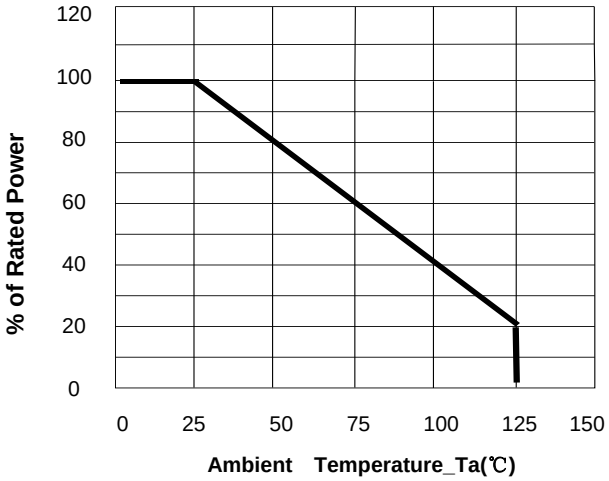
Junction Capacitance vs. Reverse Voltage



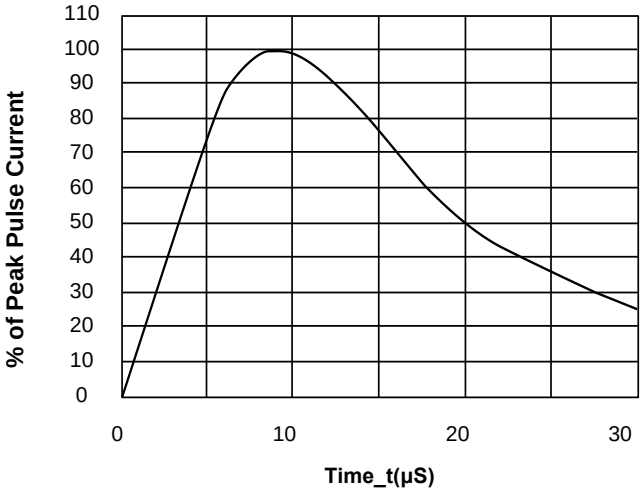
Peak Pulse Power vs. Pulse Time



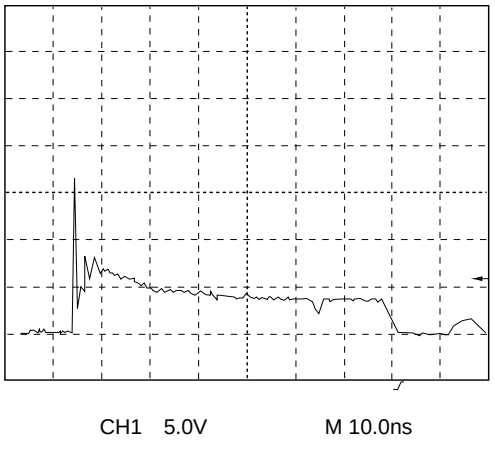
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



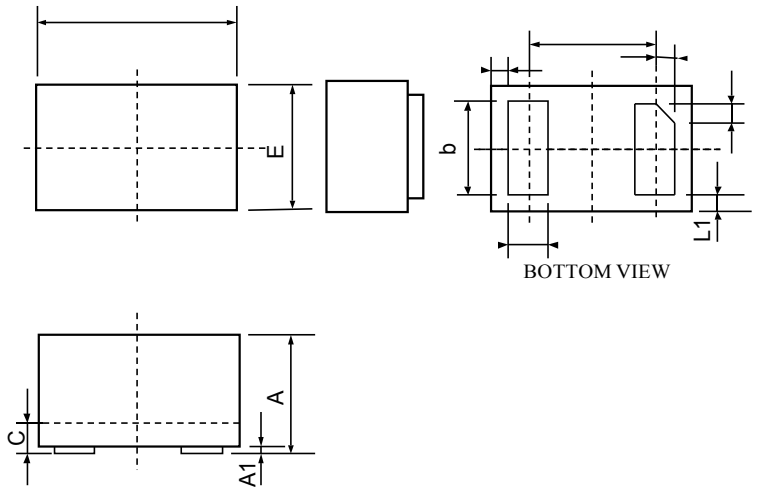
8 X 20uS Pulse Waveform



ESD Clamping Voltage

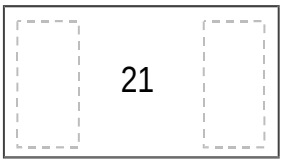
8 kV Contact per IEC61000−4−2

DFN1006-2 Package Outline Drawing



SYMBOL	MILIMETER		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17

Marking



Ordering information

Order code	Package	Baseqt	Deliverymode
PESDR0521P1	DFN1006-2	10000	Tape and reel